

Low-temperature test equipment

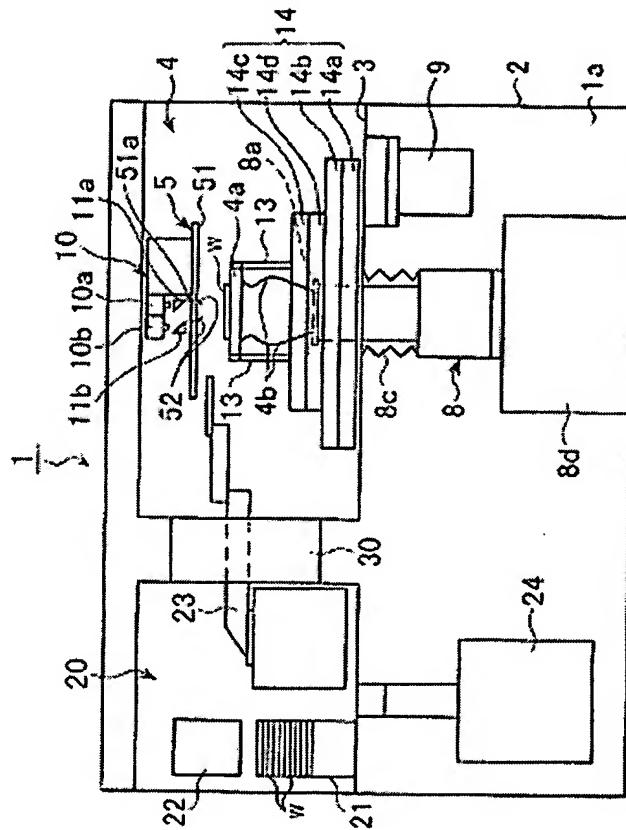
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Inventor: YAMAZAKI HIROSHI (JP)
Applicant: NAGASE & CO LTD (US)
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Abstract of US2002011835

A low-temperature test equipment capable of monitoring a test under vacuum and low temperature or ultra-low temperature conditions. The test equipment includes plural CCD cameras so arranged that plane positions thereof are rendered different from each other, as well as a prism mechanism constructed and arranged so as to permit any of the cameras to photograph a surface of a semiconductor wafer and/or a range of at least a part of probe needles of a prober. This permits a test for the wafer by the prober under vacuum and low temperature or ultra-low temperature conditions to be monitored. Also, it facilitates positional registration between the probe needles and the wafer and ensures an increase in accuracy of the test. In addition, when the low-temperature test equipment is configured so as to carry out the test in a continuous manner, full automation of the test may be realized.



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